

## Edge Illuminated InGaAs Photodiode

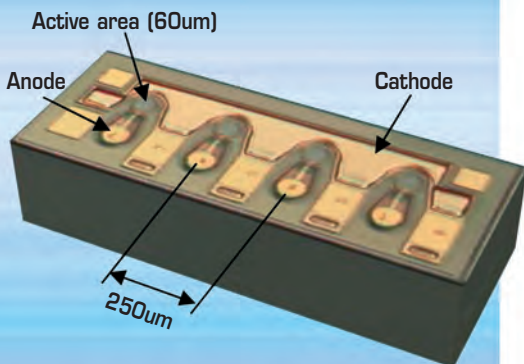
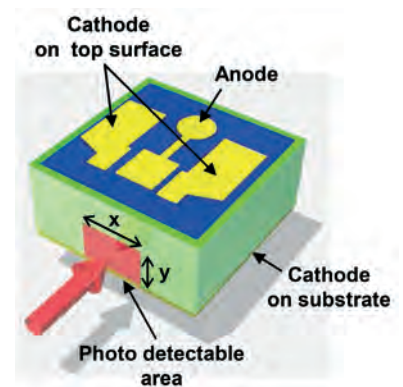
The brand new EIPD has the sensitive area on the photodiode chip edge facet. This is attractive for surface hybrid integration used with V-groove silicon or planar lightwave circuits (PLC).

### Features:

- chip size: 350 x 350 x 150µm
- active area: 80 x 80µm up to 100 x 80µm
- responsivity: 0,80 A/W (typ)
- bandwidth: 2.5Ghz (typ)
- operating temperature: -40 to +85degC

### Applications:

- laser back light power monitor
- FTTH
- optical interconnect



## NEW 10Gb PD chips / arrays for 850, 1310 and 1550nm

With the brand new GaAs PD array, Kyosemi target the short range (SR) applications of the high speed fiber optic interconnects. The active area is 60um with a responsivity of 0.6A/W (typ). The pitch is 250um.

For 1310 and 1550nm applications there is a InGaAs array with a responsivity of 0.95A/W (typ)

### Features:

- high speed
- large active diameter
- flip chip mountable

### Applications:

- optical interconnect
- fiber channel

